

# **PSMN013-100ES**

# N-channel 100V 13.9m $\Omega$ standard level MOSFET in I2PAK. Rev. 3 — 29 September 2011 Product data s

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel enhancement MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Table 1.	Quick reference da	ta					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	68	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ or } $		-	-	25	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	[2]	-	11	13.9	mΩ
Dynamic o	characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 50 \text{ V}; \text{see } \underline{\text{Figure 14}};$ $\text{see } \underline{\text{Figure 13}}$		-	17	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{G(tot)}$	total gate charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 50 \text{ V}; \text{ see } \frac{\text{Figure 13}}{\text{Figure 14}};$	-	59	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 68 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	-	127	mJ

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D D
3	S	source		$G \longrightarrow \overline{A}$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT226 (I2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN013-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

<sup>[2]</sup> Measured 3 mm from package.

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

0	Danamatan	0		B.4.:	NA	11!1
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	47	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	68	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	170	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	68	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
Avalanche rug	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 68 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	127	mJ

#### [1] Continuous current is limited by package.

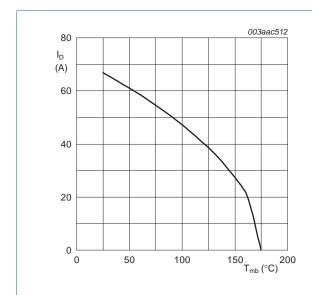


Fig 1. Continuous drain current as a function of mounting base temperature

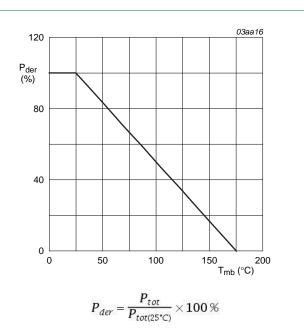


Fig 2. Normalized total power dissipation as a function of mounting base temperature

### 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 3	-	0.5	0.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

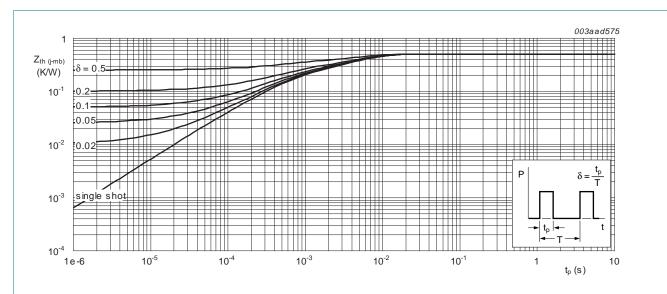


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

# 6. Characteristics

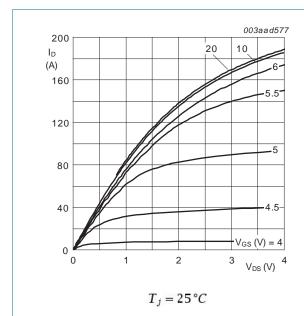
Table 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$		90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 9		1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 9</u>		2	3	4	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 10		-	-	4.8	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 ^{\circ}\text{C}$		-	-	100	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		•	0.06	2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		•	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		•	10	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 11		•	30	38.9	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 11		•	-	25	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 11	<u>[1]</u>	-	11	13.9	mΩ
$R_{G}$	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic (	characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 13; see Figure 14	,	-	59	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		-	47.6	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 13; see Figure 14		-	13.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	,	•	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge			•	4.6	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 13	,	•	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 13</u>	,	•	4.4	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	3195	-	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>		-	221	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	136	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$		-	20.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$		-	25	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	52.5	-	ns
t <sub>f</sub>	fall time			_	24	-	ns

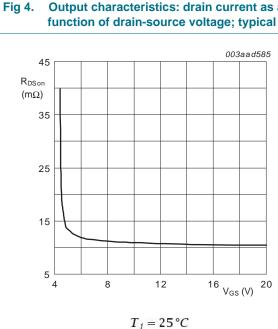
Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 16</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = 100 \text{ A/}\mu\text{s}$ ;	-	52	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	109	-	nC

#### [1] Measured 3 mm from package.



Output characteristics: drain current as a function of drain-source voltage; typical values



Drain-source on-state resistance as a function of gate-source voltage; typical values

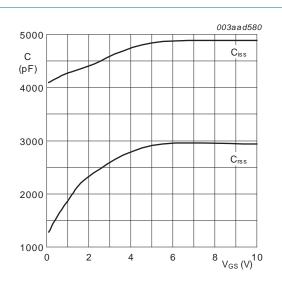


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$ 

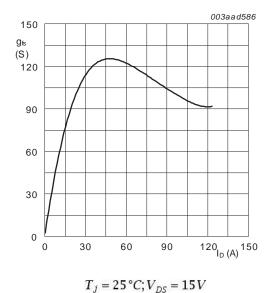


Fig 7. Forward transconductance as a function of drain current; typical values

PSMN013-100ES

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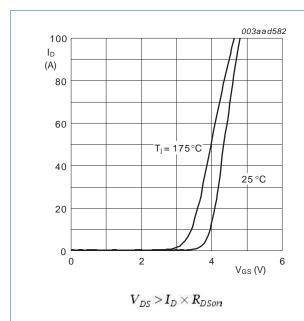


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

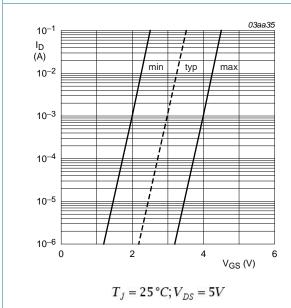


Fig 10. Sub-threshold drain current as a function of gate-source voltage

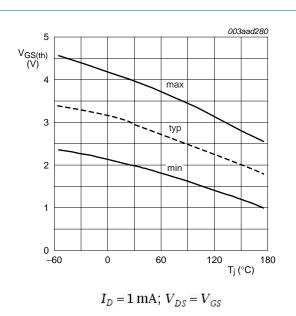


Fig 9. Gate-source threshold voltage as a function of junction temperature

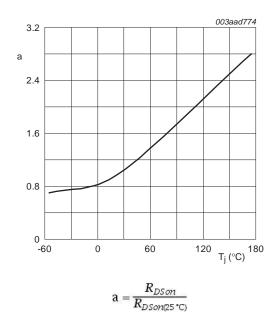


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

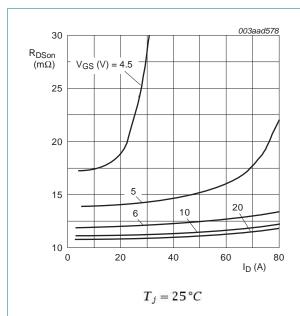


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

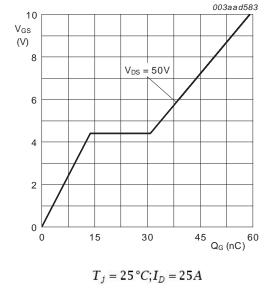


Fig 13. Gate-source voltage as a function of gate charge; typical values

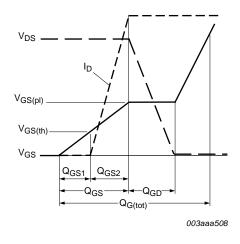


Fig 14. Gate charge waveform definitions

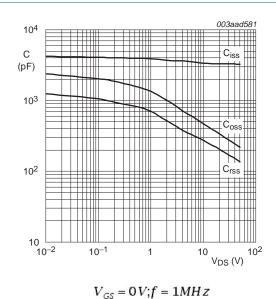


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

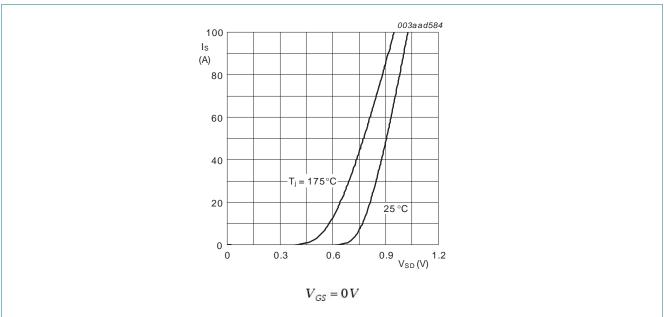


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline

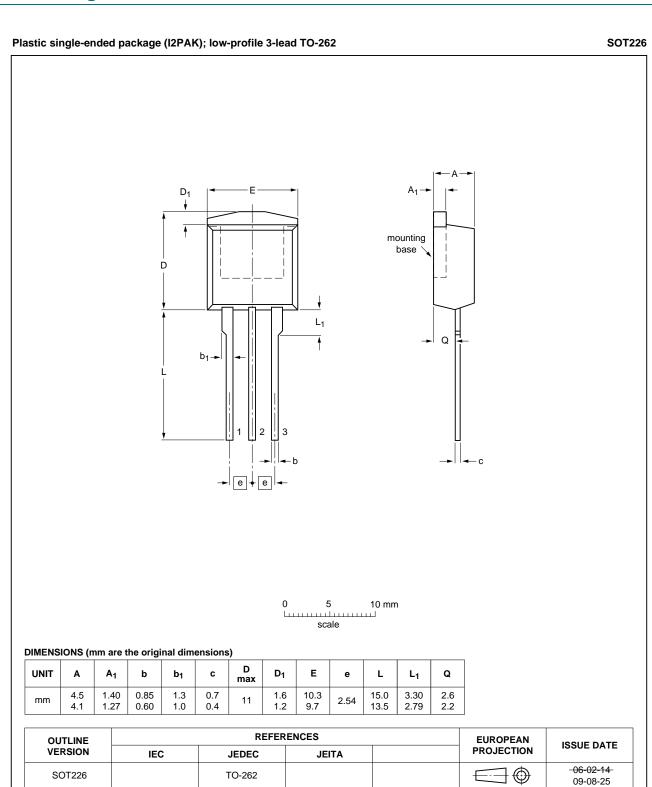


Fig 17. Package outline SOT226 (I2PAK)

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN013-100ES v.3	20110929	Product data sheet	-	PSMN013-100ES v.2	
Modifications:  • Status changed from objective to product.					
	<ul> <li>Various changes t</li> </ul>	o content.			
PSMN013-100ES v.2	20100219	Objective data sheet	-	PSMN013-100ES v.1	

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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